TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

155391

LOW VOLTAGE HIGH SPEED SWITCHING

• Low Forward Voltage : $V_{F(2)} = 0.23V$ (Typ.) @ $I_F = 5mA$

• Small Package : SC-61

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	v_{RM}	15	V
Reverse Voltage	v_{R}	10	V
Maximum (Peak) Forward Current	I_{FM}	200 ※	mA
Average Forward Current	IO	100 ※	mA
Surge Current (10ms)	I_{FSM}	1 ※	A
Power Dissipation	P	150	mW
Junction Temperature	T_{j}	125	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	$^{\circ}\mathrm{C}$
Operating Temperature Range	$T_{ m opr}$	-40~100	°C

※: Unit Rating. Total Rating=Unit Rating × 1.5

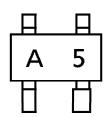
Unit in mm 2.9-0.3 0.55 0.85 1.50-0.15 1. CATHODE 1 2. CATHODE 2 3. ANODE 2 4. ANODE 1 SMQ JEDEC EIAJ SC-61 TOSHIBA 2-3J1A

Weight: 0.013g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

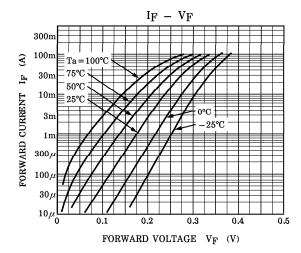
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	$I_{\mathbf{F}} = 1 \text{mA}$		0.18		V
	$V_{F(2)}$	$I_{\mathbf{F}} = 5 \text{mA}$	_	0.23	0.30	V
	$V_{F(3)}$	$I_{ m F}\!=\!100{ m mA}$		0.35	0.50	V
Reverse Current	$I_{ m R}$	$V_{ m R}$ = 10 V	_	_	20	μ A
Total Capacitance	$\mathbf{c_T}$	$V_R = 0$, $f = 1MHz$	_	20	40	рF

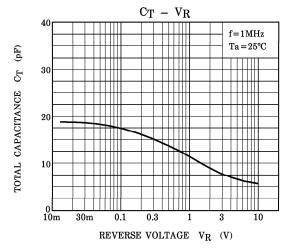
MARKING

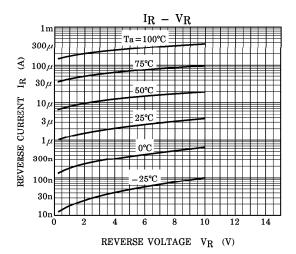


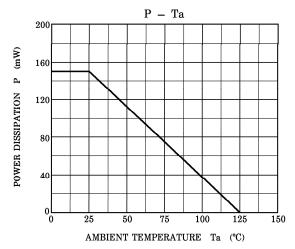
961001EAA2

[■] TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.









The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

The information contained herein is subject to change without notice.